



3DD507

NPN Silicon Low Frequency High Power Transistor



Features:

1. Three pins isn't connected with the cover. It could be produced according to the requirement.
2. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
3. Use for Low-speed switch,low frequency power amplify,power adjustment.
4. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA:

(Ta = 25°C)

Parameter name	Symbols	Unit	Specifications	Test Condition
Collector-Emitter Voltage	V _{CEO}	V	200	
Emitter-Base Voltage	V _{EBO}	V	5	
Max. Collector Current	I _{CM}	A	2	
Max. Collector Dissipation	P _{CM}	W	20	(Tc=75°C)
Junction Temperature	T _{jm}	°C	175	
Storage Temperature	T _{stg}	°C	-55~+175	
Collector-Emitter Leakage Current	I _{CEO}	mA	Max.:3.0	V _{CE} =100V
Collector- Emitter Saturation Voltage Drop	V _{CE(sat)}	V	Max.:1.0	I _c =1.0A,I _B =0.1A
DC Current Gain	h _{FE}		Min.:10	V _{CE} = 5V, I _c =1A
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	V	200	I _c =1mA
E-Base Breakdown Voltage	V _{(BR)EBO}	V	5	I _E =0.5mA

Outline and Dimensions:

